

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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## Title of Invention

METHOD FOR GROWING A GATE OXIDE LAYER ON A  
SILICON SURFACE WITH PRELIMINARY N2O ANNEAL

Application Number :

Confirmation Number:

First Named Applicant: Shian-Jyh Lin

Attorney Docket Number: NTCP0014USA

Art Unit:

Examiner:

Search string: ( 6184110 or 6204205 or 6498365 ).pn

## US Patent Documents

**Note: Applicant is not required to submit a paper copy of cited US Patent Documents**

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6184110	2001-02-06	Ono, et al.			
	2	6204205	2001-03-20	Yu, et al.			
	3	6498365	2002-12-24	Wakamiya			

## Signature

Examiner Name	Date